



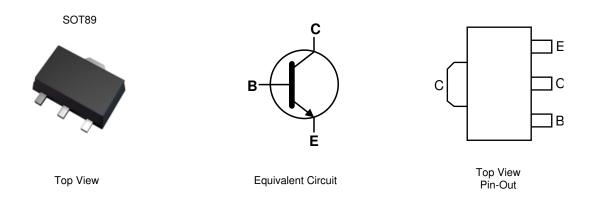
400V NPN HIGH VOLTAGE TRANSISTOR IN SOT89

Features

- BV_{CEO} > 400V
- I_C = 225mA Continuous Collector Current
- I_{CM} = 500mA Peak Pulse Current
- Excellent h_{FE} Characteristics up to 100mA
- Low saturation voltage V_{CE(sat)} < 200mV @ 20mA
- Complementary PNP Type: FCX558
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.055 grams (Approximate)



Ordering Information (Note 4)

| Product | Compliance | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|----------|------------|---------|--------------------|-----------------|-------------------|
| FCX458TA | AEC-Q101 | N58 | 7 | 12mm | 1,000 |

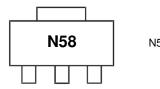
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.

3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



N58 = Product Type Marking Code



Absolute Maximum Ratings (@T_{A = +25°C}, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage | V _{CBO} | 400 | V |
| Collector-Emitter Voltage | V _{CEO} | 400 | V |
| Emitter-Base Voltage | V _{EBO} | 7 | V |
| Continuous Collector Current | lc | 225 | mA |
| Peak Pulse Current | I _{CM} | 500 | mA |
| Base Current | IB | 200 | mA |

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | | |
|---|----------|----------------------------------|-------------|------|--|
| | (Note 5) | | 0.7 | | |
| Device Disaination | (Note 6) | PD | 1 | W | |
| Power Dissipation | (Note 7) | | 1.5 | | |
| | (Note 8) | | 2 | | |
| | (Note 5) | R _{0JA} | 178 | | |
| Thermal Desistance, lunction to Ambient Air | (Note 6) | | 125 | | |
| Thermal Resistance, Junction to Ambient Air | (Note 7) | | 83 | °C/W | |
| | (Note 8) | | 60 | | |
| Thermal Resistance, Junction to Lead | (Note 9) | R _{θJL} | 22 | | |
| Operating and Storage Temperature Range | | T _{J,} T _{STG} | -65 to +150 | °C | |

ESD Ratings (Note 10)

Notes:

| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V | ЗA |
| Electrostatic Discharge - Machine Model | ESD MM | 400 | V | С |

5. For a device mounted with the exposed collector pad on minimum recommended pad layout (MRP) 1oz copper that is on a single-sided

1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

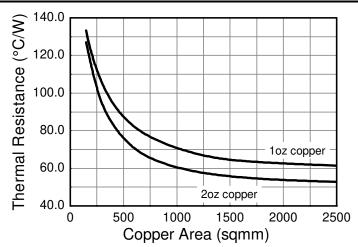
6. Same as Note 5, except the device is mounted with the exposed collector pad on 15mm x 15mm 1oz copper.

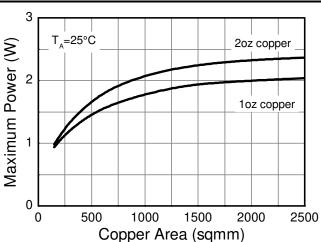
7. Same as Note 5, except the device is mounted with the exposed collector pad on 25mm x 25mm 1oz copper.

8. Same as Note 5, except the device is mounted with the exposed collector pad on 50mm x 50mm 1oz copper.

Thermal resistance from junction to solder-point (on the exposed collector pad).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information







Thermal Characteristics and Derating Information (cont.) 1.2 Max Power Dissipation (W) 15mm x 15mm 1oz FR4 PCB MRP 1oz FR4 PCB 1.0 0.8 0.6 0.4 0.2 0.0 40 60 80 100 Temperature (°C) 60 80 100 140 140 20 40 120 160 20 40 120 160 Temperature (°C) **Derating Curve Derating Curve** 100 130 120 15mm x 15mm 1oz FR4 PCB 15mm x 15mm 1oz FR4 PCB Thermal Resistance (°C/W) 110 Maximum Power (W) Single Pulse 100 90 T_=25°C 80 D=0.5 70 60 50 40 Single Pulse D=0.2 30 D=0.05 20 D=0.1 10m 100m 1 Pulse Width (s) 100µ 10m 100m 1 1 Pulse Width (s) 10 100 100µ 100 1m 1m 10 **Transient Thermal Impedance Pulse Power Dissipation** 180 100 MRP 1oz FR4 PCB 160 MRP 1oz FR4 PCB Thermal Resistance (°C/W) -----Maximum Power (W) 140 Single Pulse T_A=25°C 120 100 D=0.5 10 80 60 Single Pulse D=0.2 D=0.05 D=0.1 100µ 0m 100m 1 Pulse Width (s) 10m 100 10m 100m 1m 10 10<mark>0</mark>μ 100 1m 10 Γk Pulse Width (s) **Transient Thermal Impedance Pulse Power Dissipation**



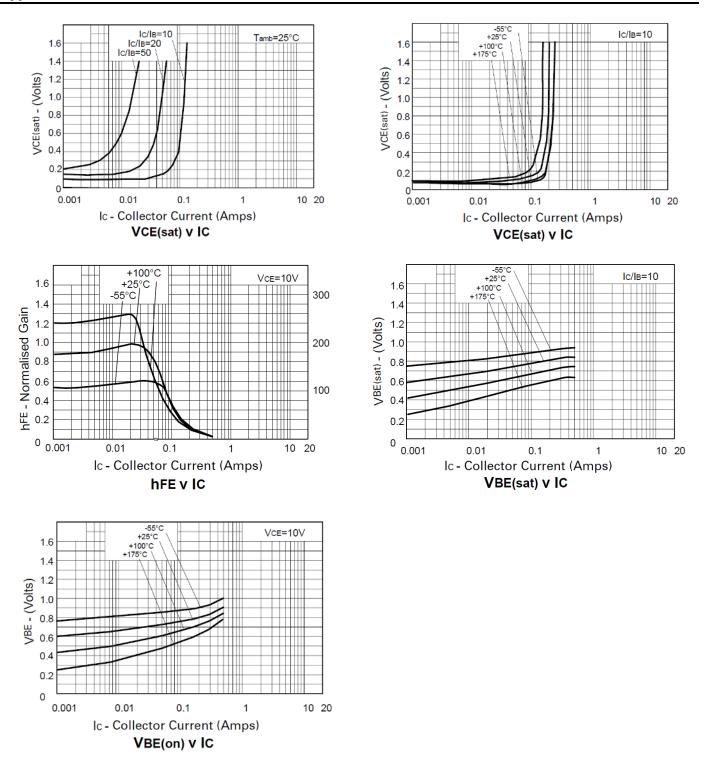
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Мах | Unit | Test Condition |
|--|----------------------|------------------|------|------------|------|--|
| Collector-Base Breakdown Voltage | BV _{CBO} | 400 | 550 | _ | V | I _C = 100μA |
| Collector-Emitter Breakdown Voltage | BV _{CES} | 400 | 550 | | V | I _C = 100μA |
| Collector-Emitter Breakdown Voltage (Note 11) | BV _{CEO} | 400 | 450 | _ | V | I _C = 1mA |
| Emitter-Base Breakdown Voltage | BV _{EBO} | 7 | 8.1 | | V | I _E = 100μA |
| Collector-Base Cutoff Current | I _{СВО} | — | <1 | 100 | nA | V _{CB} = 320V |
| Collector Cutoff Current | I _{CES} | — | <1 | 100 | nA | V _{CES} = 320V |
| Emitter Cutoff Current | I _{EBO} | — | <1 | 20 | nA | $V_{EB} = 6V$ |
| Collector-Emitter Saturation Voltage (Note 11) | V _{CE(sat)} | _ | _ | 200 500 | mV | $I_{C} = 20mA, I_{B} = 2mA$ $I_{C} = 50mA, I_{B} = 6mA$ |
| Base-Emitter Saturation Voltage (Note 11) | V _{BE(sat)} | _ | _ | 900 | mV | $I_{\rm C} = 50 {\rm mA}, I_{\rm B} = 5 {\rm mA}$ |
| Base-Emitter Turn-On Voltage (Note 11) | V _{BE(on)} | _ | _ | 900 | mV | $I_{C} = 50 \text{mA}, V_{CE} = 10 \text{V}$ |
| DC Current Gain (Note 11) | hFE | 100 100 15 | | 300 | _ | $\label{eq:lc} \begin{split} I_{C} &= 1mA, V_{CE} = 10V \\ I_{C} &= 50mA, V_{CE} = 10V \\ I_{C} &= 100mA, V_{CE} = 10V \end{split}$ |
| Transitional Frequency | f _T | 50 | _ | _ | MHz | $I_{C} = 10 \text{mA}, V_{CE} = 20 \text{V},$ f = 20MHz |
| Output Capacitance | C _{obo} | _ | _ | 5 | pF | V _{CB} = 20V. f = 1MHz |
| Turn-On Time | t _{on} | — | 135 | _ | ns | I _C =50mA, V _{CE} =100V, |
| Turn-Off Time | t _{off} | _ | 2260 | _ | ns | I _{B1} = 5mA, I _{B2} = -10mA |

Note: 11. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%



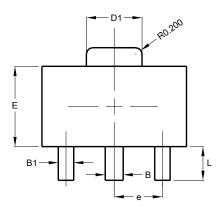
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

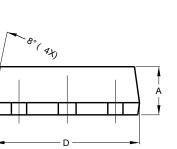


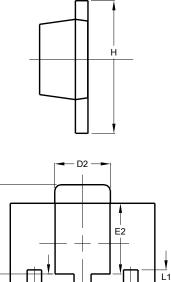


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.







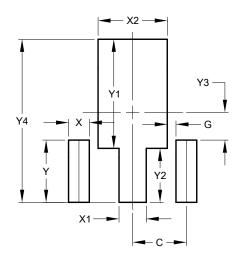
С

| SOT89 | | | | | |
|-------|--------|----------|-------|--|--|
| Dim | Min | Max | Тур | | |
| Α | 1.40 | 1.60 | 1.50 | | |
| В | 0.50 | 0.62 | 0.56 | | |
| B1 | 0.42 | 0.54 | 0.48 | | |
| С | 0.35 | 0.43 | 0.38 | | |
| D | 4.40 | 4.60 | 4.50 | | |
| D1 | 1.62 | 1.83 | 1.733 | | |
| D2 | 1.61 | 1.81 | 1.71 | | |
| ш | 2.40 | 2.60 | 2.50 | | |
| E2 | 2.05 | 2.35 | 2.20 | | |
| е | - | - | 1.50 | | |
| н | 3.95 | 4.25 | 4.10 | | |
| H1 | 2.63 | 2.93 | 2.78 | | |
| L | 0.90 | 1.20 | 1.05 | | |
| L1 | 0.327 | 0.527 | 0.427 | | |
| z | 0.20 | 0.40 | 0.30 | | |
| All | Dimens | sions in | mm | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

H1



| Dimensions | Value | | |
|------------|---------|--|--|
| Dimensions | (in mm) | | |
| С | 1.500 | | |
| G | 0.244 | | |
| Х | 0.580 | | |
| X1 | 0.760 | | |
| X2 | 1.933 | | |
| Y | 1.730 | | |
| Y1 | 3.030 | | |
| Y2 | 1.500 | | |
| Y3 | 0.770 | | |
| Y4 | 4.530 | | |

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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